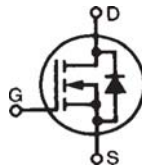


# High Voltage Power MOSFET

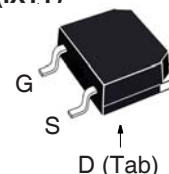
# IXTT1N450HV IXTH1N450HV

$V_{DSS} = 4500V$   
 $I_{D25} = 1A$   
 $R_{DS(on)} \leq 80\Omega$

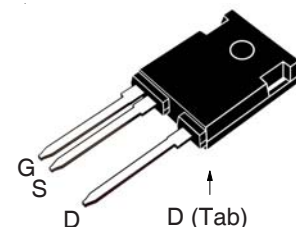
N-Channel Enhancement Mode



TO-268HV (IXTT)



TO-247HV (IXTH)



G = Gate      D = Drain  
 S = Source    Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	4500	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	4500	V
$V_{GSS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ C$	1	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	3	A
$P_D$	$T_C = 25^\circ C$	520	W
$T_J$		- 55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		- 55 ... +150	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
$F_C$	Mounting Force (TO-263HV)	10..65 / 22..14.6	N/lb
$M_d$	Mounting Torque (TO-247HV)	1.13/10	Nm/lb.in
<b>Weight</b>	TO-263HV	2.5	g
	TO-247HV	6.0	g

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	3.5		6.0 V
$I_{GSS}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 100$ nA
$I_{DSS}$	$V_{DS} = 3.6kV$ , $V_{GS} = 0V$ $V_{DS} = 4.5kV$ $V_{DS} = 3.6kV$ $T_J = 100^\circ C$			5 $\mu A$
				25 $\mu A$
				15 $\mu A$
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 50mA$ , Note 1			80 $\Omega$

## Features

- High Blocking Voltage
- High Voltage Package

## Advantages

- Easy to Mount
- Space Savings
- High Power Density

## Applications

- High Voltage Power Supplies
- Capacitor Discharge Applications
- Pulse Circuits
- Laser and X-Ray Generation Systems

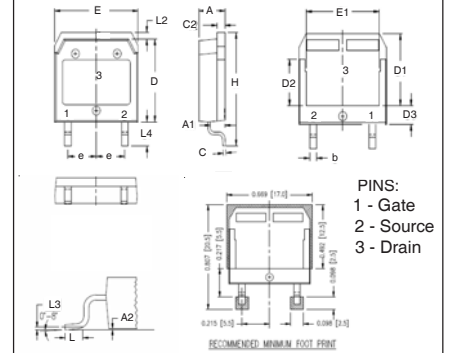
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 50\text{V}$ , $I_D = 200\text{mA}$ , Note 1	0.40	0.70	S
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		1700	pF
$C_{oss}$			80	pF
$C_{rss}$			29	pF
$R_{Gi}$	Gate Input Resistance		12	$\Omega$
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}$ , $V_{DS} = 500\text{V}$ , $I_D = 0.5 \cdot I_{D25}$ $R_G = 10\Omega$ (External)		30	ns
$t_r$			43	ns
$t_{d(off)}$			73	ns
$t_f$			120	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 1\text{kV}$ , $I_D = 0.5 \cdot I_{D25}$		46	nC
$Q_{gs}$			8	nC
$Q_{gd}$			23	nC
$R_{thJC}$	TO-247HV		0.24	$^\circ\text{C/W}$
$R_{thCS}$			0.21	$^\circ\text{C/W}$

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			1 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			5 A
$V_{SD}$	$I_F = 1\text{A}$ , $V_{GS} = 0\text{V}$ , Note 1			2.0 V
$t_{rr}$	$I_F = 1\text{A}$ , $-di/dt = 50\text{A}/\mu\text{s}$ , $V_R = 100\text{V}$		1.75	$\mu\text{s}$

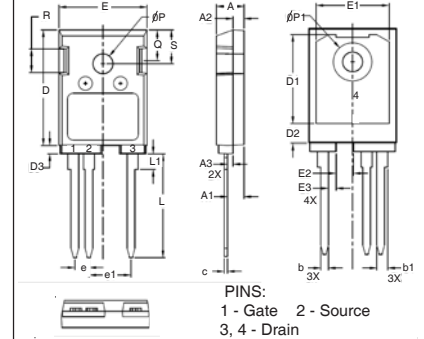
Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

### TO-268HV Outline



SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.465	.476	11.80	12.10
D2	.295	.307	7.50	7.80
D3	.114	.126	2.90	3.20
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
E	.215	BSC	5.45	BSC
H	.736	.752	18.70	19.10
L	.067	.079	1.70	2.00
L2	.039	.045	1.00	1.15
L3	.010	BSC	0.25	BSC
L4	.150	.161	3.80	4.10

### TO-247HV Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.114	.122	2.90	3.10
A2	.075	.083	1.90	2.10
A3	.035	.043	0.90	1.10
b	.053	.059	1.35	1.50
b1	.075	.083	1.90	2.10
c	.022	.030	0.55	0.75
D	.819	.843	20.80	21.40
D1	.638	.646	16.20	16.40
D2	.134	.146	3.40	3.70
D3	.055	.063	1.40	1.60
E	.622	.638	15.80	16.20
E1	.520	.528	13.20	13.40
E2	.118	.126	3.00	3.20
E3	.051	.059	1.30	1.50
e	.100	BSC	2.54	BSC
e1	.300	BSC	7.62	BSC
L	.732	.748	18.60	19.00
L1	.106	.118	2.70	3.00
ØP	.138	.142	3.50	3.60
ØP1	.272	.280	6.90	7.10
Q	.216	.224	5.50	5.70
R	.165	.169	4.20	4.30
S	.240	.248	6.10	6.30

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$

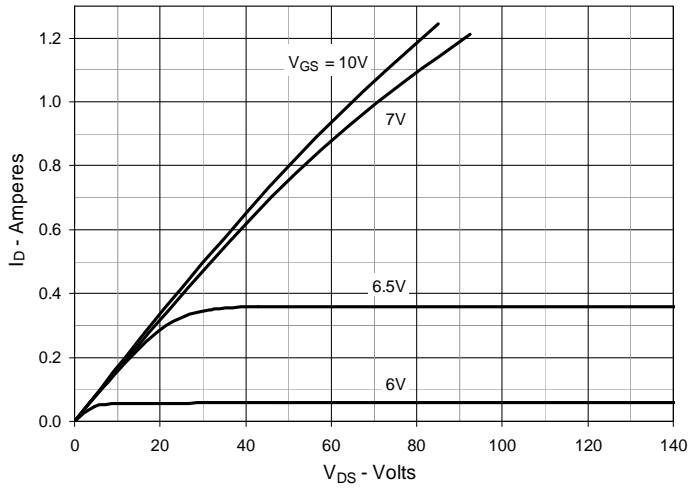


Fig. 2. Output Characteristics @  $T_J = 125^\circ\text{C}$

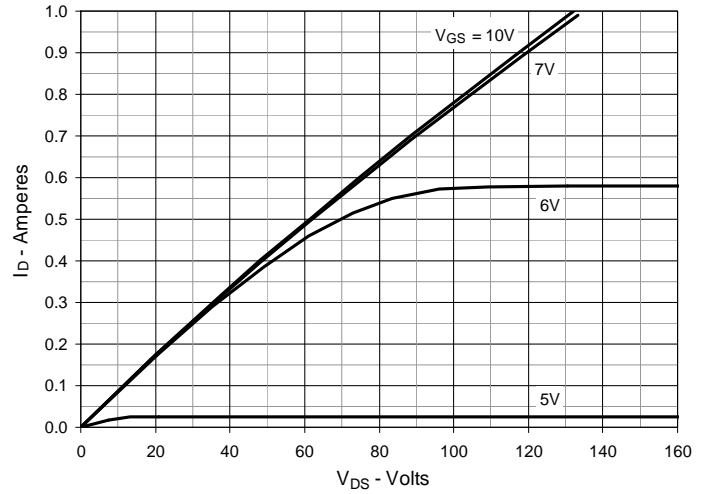


Fig. 3.  $R_{DS(on)}$  Normalized to  $I_D = 0.5\text{A}$  Value vs. Junction Temperature

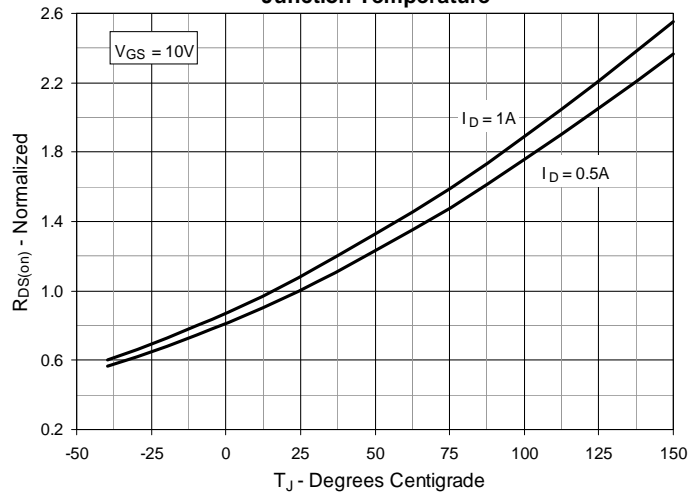


Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 0.5\text{A}$  Value vs. Drain Current

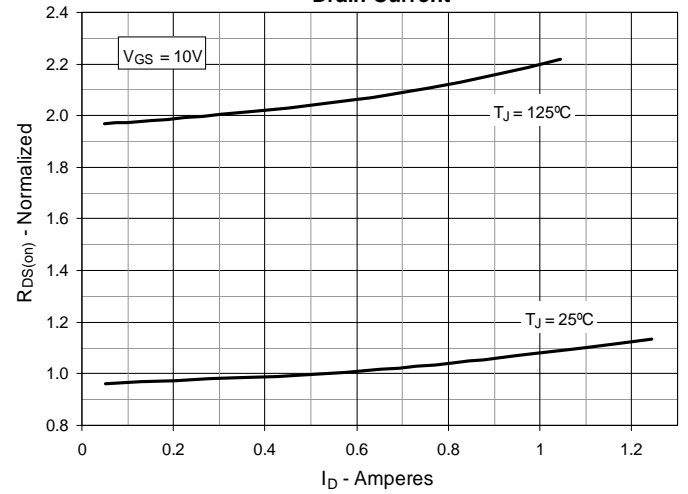


Fig. 5. Maximum Drain Current vs. Case Temperature

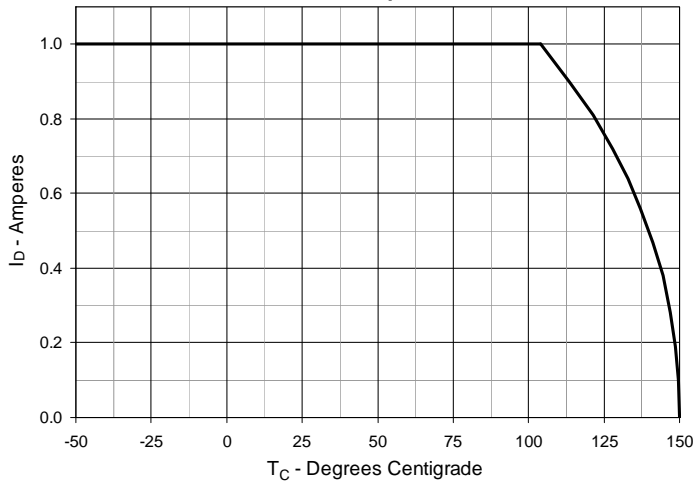


Fig. 6. Input Admittance

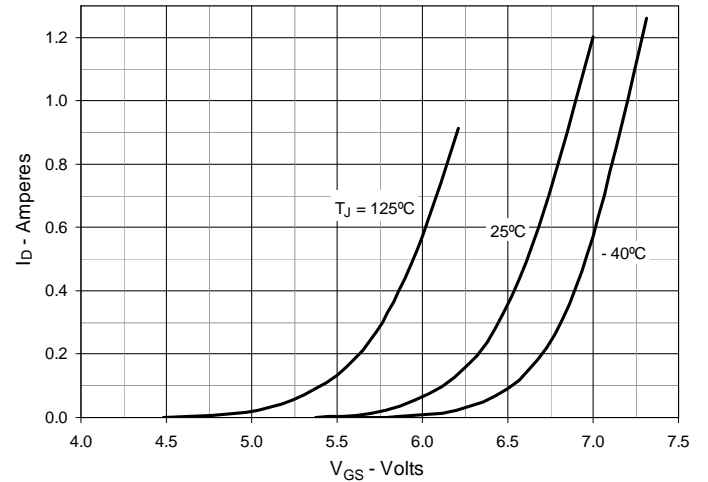


Fig. 7. Transconductance

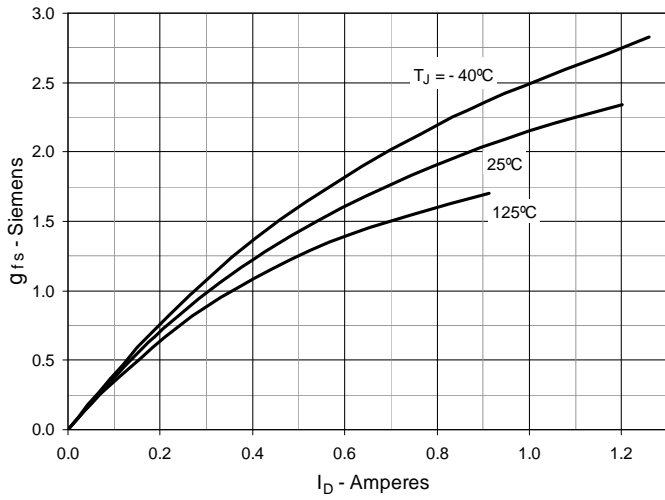


Fig. 8. Forward Voltage Drop of Intrinsic Diode

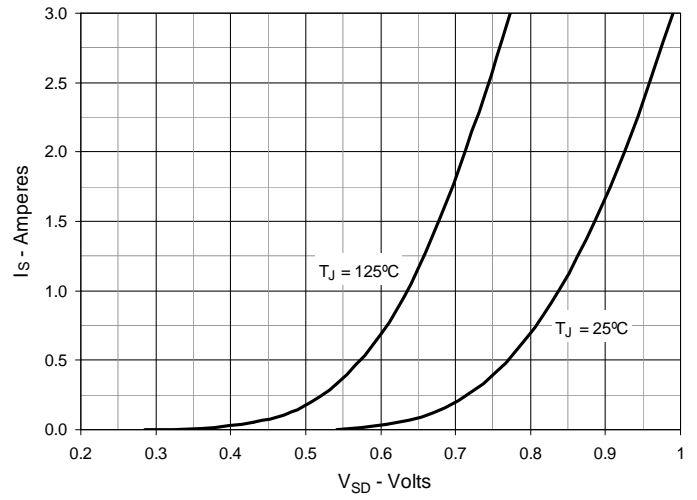


Fig. 9. Gate Charge

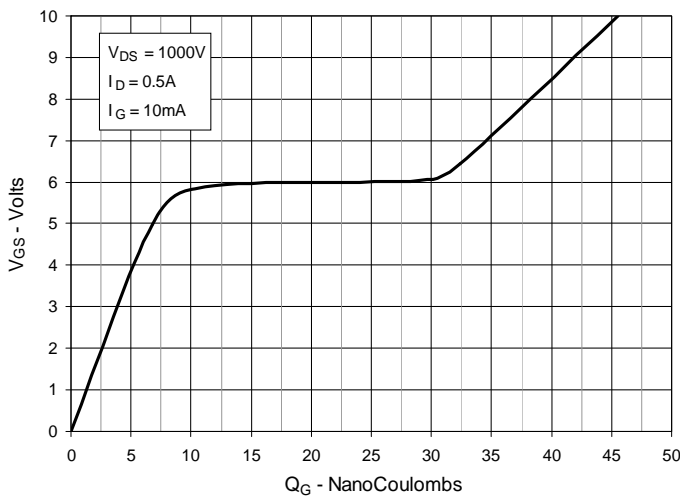


Fig. 10. Capacitance

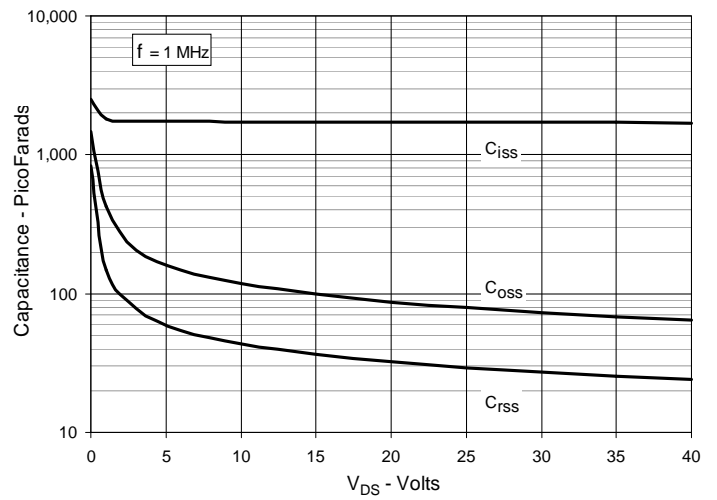


Fig. 11. Maximum Transient Thermal Impedance

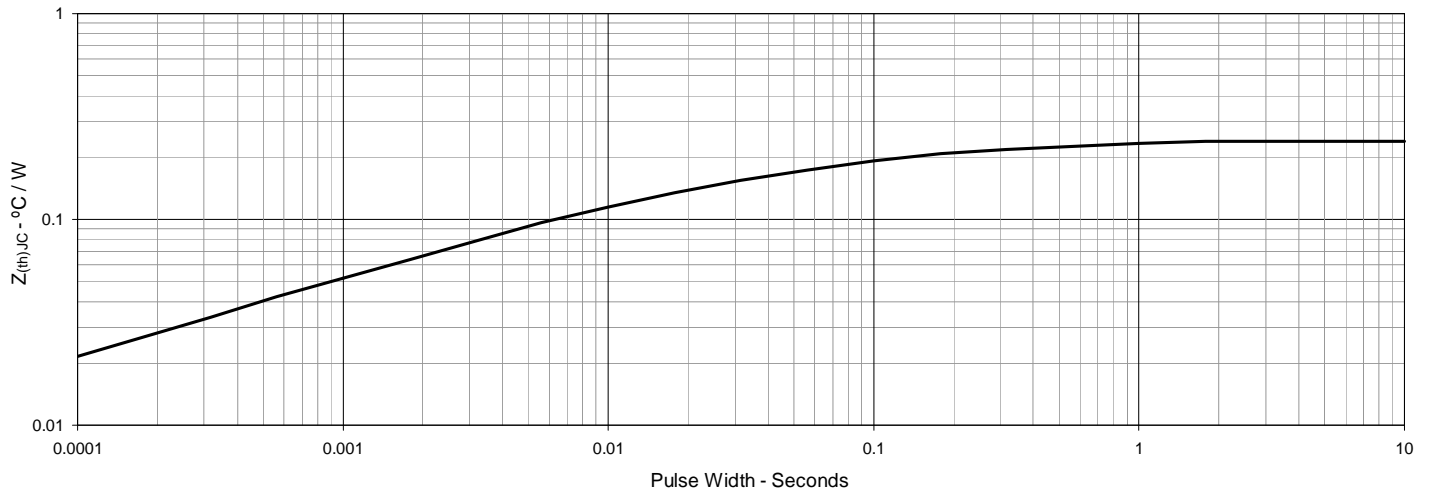


Fig. 12. Forward-Bias Safe Operating Area  
@  $T_C = 25^\circ\text{C}$

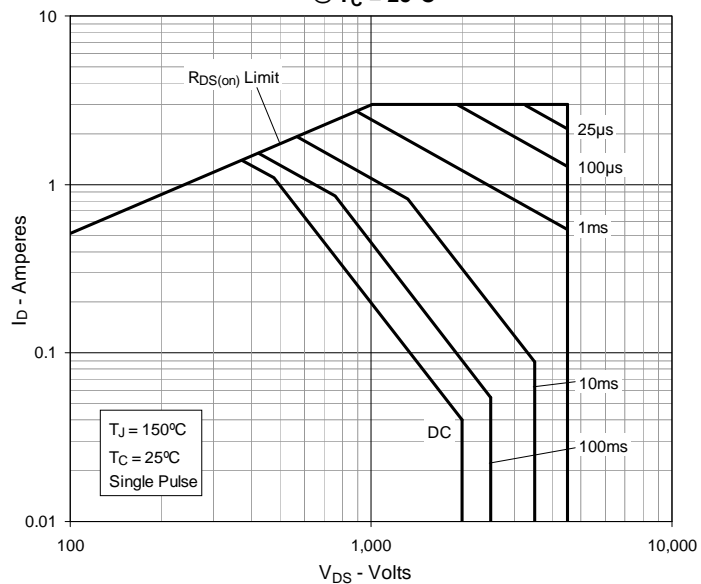
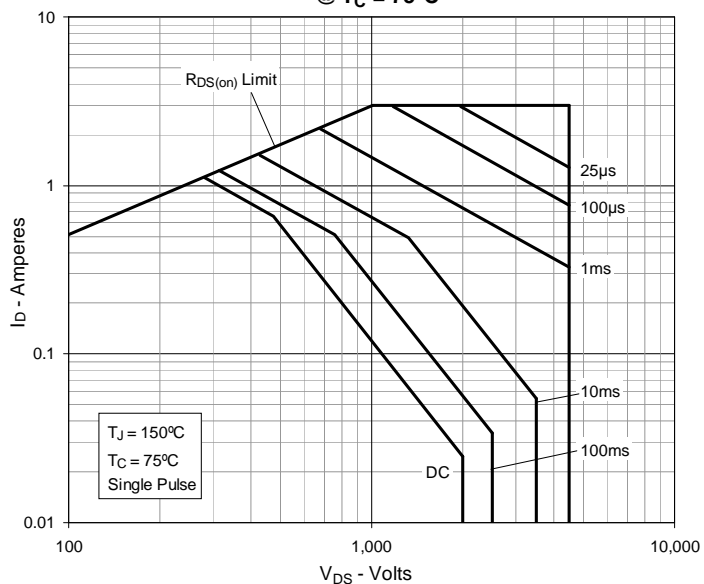


Fig. 13. Forward-Bias Safe Operating Area  
@  $T_C = 75^\circ\text{C}$





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